First Named Inventor	Leonard Forbes	JUL 1 5 2005 125
Serial No.	10/785,310	OF COMP
Filing Date	February 24, 2004	PLEMENTAL
Group Art Unit	2818	INFORMATION
Examiner Name	Tu Tu V. Ho	DISCLOSURE
Allowed	April 28, 2005	— STATEMENT
Confirmation No.	9673	
Attorney Docket No.	400.264US01	

Mail Stop: RCE

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

In compliance with 37 C.F.R. §§ 1.56 and 1.97, et seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

A copy of the International Search Report is enclosed herewith.

As this Second Supplemental Information Disclosure Statement is being filed together with a Request for Continuing Examination (RCE), Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

PAGE 2

Serial No. 10/785,310

Attorney Docket No. 400.264US01

Title: 4F2 EEPROM NROM MEMORY ARRAYS WITH VERTICAL DEVICES

If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2207.

Respectfully submitted,

Date:

Andrew C. Walseth Reg. No. 43,234

Attorneys for Applicant Leffert Jay & Polglaze P.O. Box 581009 Minneapolis, MN 55458-1009 T 612 312-2200 F 612 312-2250

First Named Inventor	Leonard Forbes	SECOND SUPPLEMENTAL	
Serial No.	10/785,310	INFORMATION DISCLOSURE	٠
Filing Date	February 24, 2004		•
Group Art Unit	2818	TP E STATEMENT	
Examiner Name	Tu Tu V. Ho	7 FORM PTO-1449	
Allowed	April 28, 2003	JUL 1 5 2005 12	
Confirmation No.	9673	اللا الله الله	
Attorney Docket No.	400.264US01	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
•	NROM MEMORY ARRAYS	Sheet 1 of	f 2
WITH VERTICAL DE	VICES		

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Signature		Considered			
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not					
in conformance and not considered. Include copy of this form with next communication to applicant.					
Based on Form PTO-FB-A820 Patent and Trademark Office, U.S. Department of Commerce					

First Named Inventor	Leonard Forbes	SECOND
Serial No.	10/785,310	INFORMAT
Filing Date	February 24, 2004	1
Group Art Unit	2818	ST
Examiner Name	Tu Tu V. Ho	FOR
Allowed	April 28, 2003	
Confirmation No.	9673	-
Attorney Docket No.	400.264US01	7
Title: 4F2 EEPROM N	ROM MEMORY ARRAYS	

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT FORM PTO-1449

Title: 4F2 EEPROM NROM MEMORY ARRAYS
WITH VERTICAL DEVICES
Sheet 2 of 2

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Signature		Considered				
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not						
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